

BTA203-800CT

3Q Hi-Com Triac Rev.02 - 10 September 2019

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO92 (SOT54) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This series triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- High blocking voltage capability
- · High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- · Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- · General purpose motor control circuits
- Home appliances
- Solenoid drivers

4. Quick reference data

	uick reference data			
Symbol	Parameter	Conditions	Values	Unit
Absolute	maximum rating			
V_{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; Fig. 1; Fig. 2; Fig. 3	3	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	30	А
state current		full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C Fig. 4; Fig. 5	27	A
Tj	junction temperature		150	°C

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
I _{GT}	gate trigger current	V_{D} = 12 V; I _T = 0.1 A; T2+ G+ T _j = 25 °C; <u>Fig. 7</u>		-	-	30	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G-}$ T _j = 25 °C; <u>Fig. 7</u>		-	-	30	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2- G-}$ T _j = 25 °C; <u>Fig. 7</u>		-	-	30	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.4	1.7	V
Dynamic	characteristics	1	1			- 1	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		2000	-	-	V/µs
		V_{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ I}_{T(RMS)} = 3 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$		5	-	-	A/ms

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		N
2	G	gate		
3	T1	main terminal 1	() () () 10-92 (SOT54)	sym051

6. Ordering information

Table 3. Ordering information							
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
BTA203-800CT	TO92	BTA203-800CTEP	Bulk	1000	SOT54	14-Nov-2013	

7. Marking

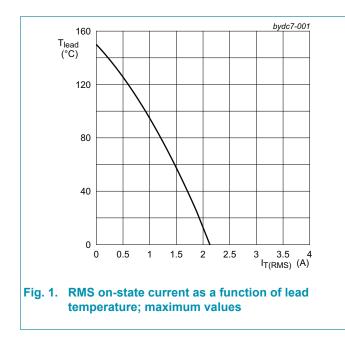
Table 4. Marking codes	
Type number	Marking codes
BTA203-800CT	203-8C

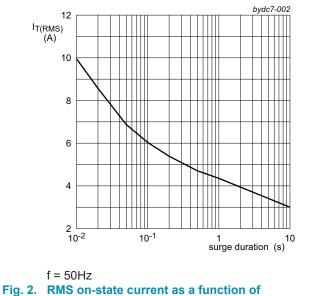
8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

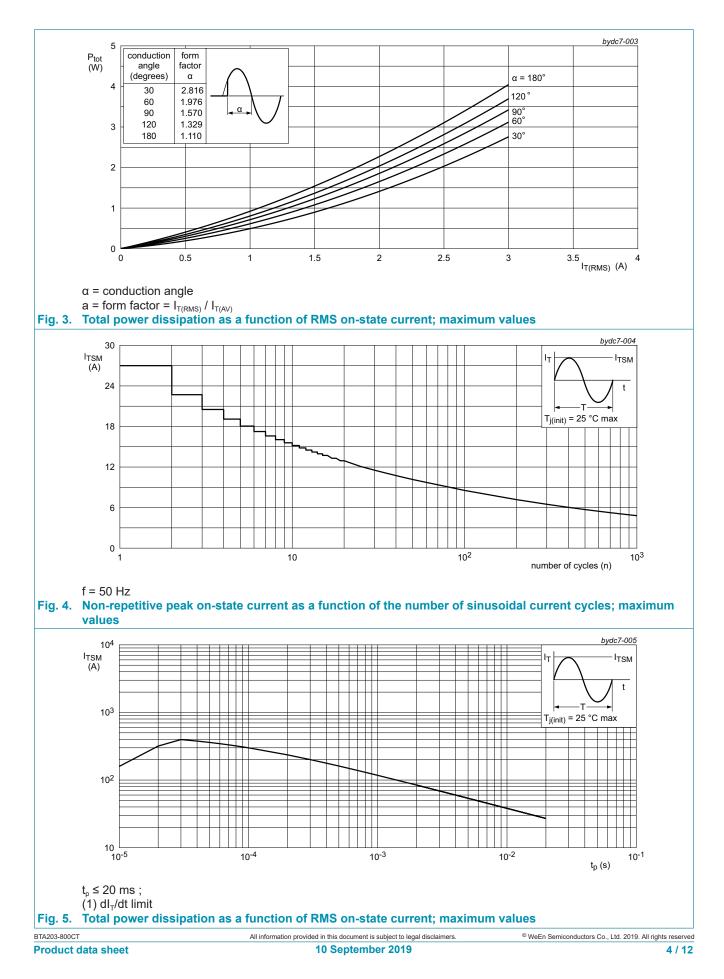
Symbol	Parameter	Conditions	Values	Unit
V _{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; Fig. 1; Fig. 2; Fig. 3	3	А
I _{TSM}	non-repetitive peak on-	full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	30	А
	state current	full sine wave; t _p = 20 ms; T _{j(init)} = 25 °C; Fig. 4; Fig. 5	27	A
l ² t	I ² t for fusing	t_p = 10 ms; sine wave	3.7	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 60 mA	100	A/µs
I _{GM}	peak gate current		2	А
P _{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.3	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C





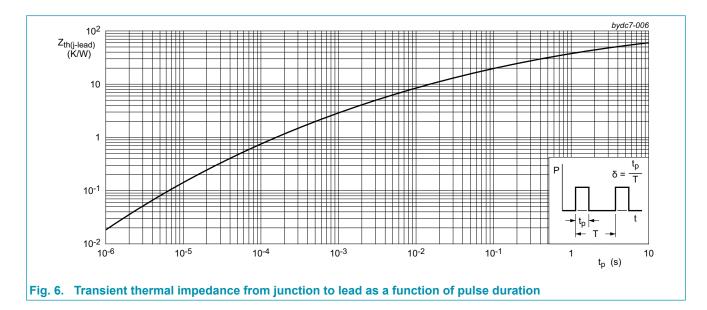
surge duration; maximum values

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9. Thermal characteristics

Table 5. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	<u>Fig. 6</u>	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	150	-	K/W

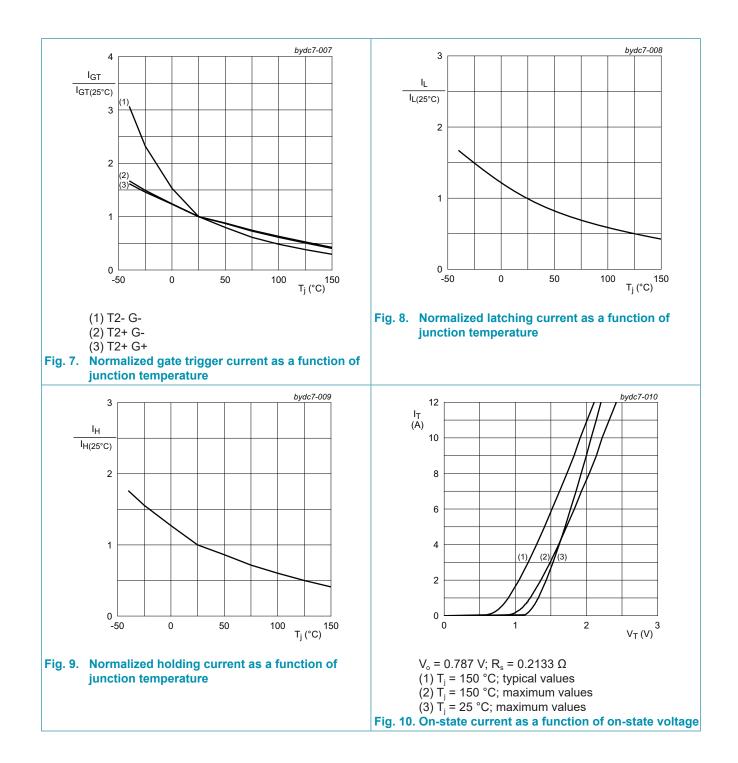


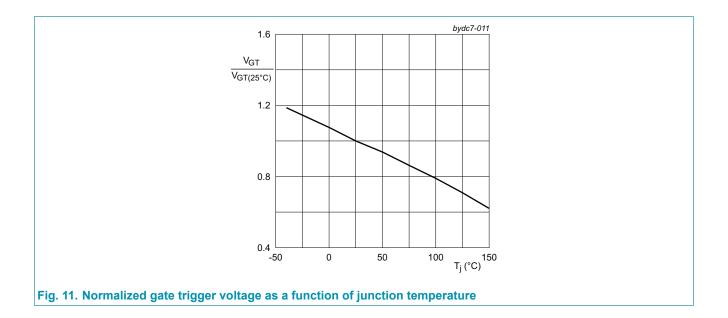
10. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics	· · · · · · · · · · · · · · · · · · ·			·		
I _{GT}	gate trigger current	V_{D} = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>		-	-	30	mA
		V_{D} = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>		-	-	30	mA
		V_{D} = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		-	-	30	mA
IL I	latching current	V_{D} = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8		-	-	30	mA
		V_{D} = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>		-	-	60	mA
		V_{D} = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>		-	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	-	30	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>		-	1.4	1.7	V
V_{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11		-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C		0.25	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C		-	-	10	μA
		V _D = 800 V; T _j = 150 °C		-	-	0.5	mA
Dynamic o	characteristics	11	I				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		2000	-	-	V/µs
		V_{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1500	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 3 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu \text{s}; \text{ (snubberless condition); gate open circuit}$		5	-	-	A/ms

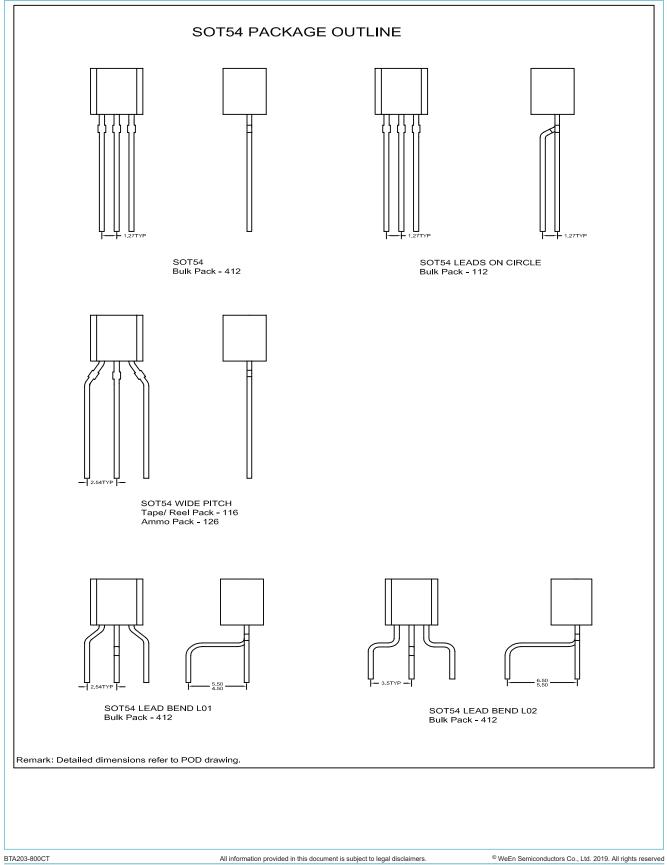
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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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